Review of: "the electric charge density increases in different areas of the nano-transistor , or in other words, the number of electric charges per unit area of the nano-transistor increases"

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> ***In the nano transistor structure, the electronic quantity that is more easily available is the ionization potential, and the ionization potential is greater in the size of the small grains of the nano structure (smaller particles), that is, as the size of the particles increases, their ionization potential decreases. Finds.***

An increase in the surface-to- volume ratio and changes in geometry and electronic structure have a strong impact on the chemical interactions of matter, and for example, the activity of small particles changes with changes in the number of atoms (and thus the size of the particles). Unlike today's nano-transistors, which behave based on the movement of a mass of electrons in matter, new devices follow the phenomena of quantum mechanics at the nano scale, in which the discrete nature of electrons cannot be ignored. By reducing all the horizontal and vertical dimensions of the transistor, the electric charge density increases in different areas of the nano-transistor , or in other words, the number of electric charges per unit area of the nano-transistor increases.This kind of integrated circuits with their unique characteristics in the nanometer scale have various applications of mesoscopic systems.Modeling Si/Cu nanoparticles based on a relationship between molecular mechanics and solid mechanics, an energy-equivalent model is used for the mechanical properties and nanomolecular structure of the sputtering layer of materials, macroscopic properties of nanoparticles such as melting point, boiling point and electrical conductivity . It is done through a sample that is large enough to be measured in normal laboratory conditions.

> ***When the melting point of a nanomolecule is measured, in fact, the behavior of a large number of nanoparticle molecules is examined, and this is not true for all materials; When the material size is reduced and reaches nanometer dimensions, completely different behavior and properties may be seen compared to the same material in large dimensions.***

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